COMPLIANT

HALOGEN

FREE



### Vishay Semiconductors

# Hyperfast Rectifier, 1 A FRED Pt®



### **LINKS TO ADDITIONAL RESOURCES**



| PRIMARY CHARACTERISTICS          |                |  |  |
|----------------------------------|----------------|--|--|
| I <sub>F(AV)</sub>               | 1 A            |  |  |
| $V_{R}$                          | 200 V          |  |  |
| V <sub>F</sub> at I <sub>F</sub> | 0.68 V         |  |  |
| t <sub>rr</sub>                  | 25 ns          |  |  |
| T <sub>J</sub> max.              | 175 °C         |  |  |
| Package                          | SMA (DO-214AC) |  |  |
| Circuit configuration            | Single         |  |  |

#### **FEATURES**

- Hyperfast recovery time, reduced Q<sub>rr</sub>, and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

#### **MECHANICAL DATA**

Case: SMA (DO-214AC)

Molding compound meets UL 94 V-0 flammability rating

Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002

Polarity: color band denotes cathode end

| ABSOLUTE MAXIMUM RATINGS                    |                                   |   |             |       |
|---|-----------------------------------|---|-------------|-------|
| PARAMETER                                   | SYMBOL                            | TEST CONDITIONS                           | VALUES      | UNITS |
| Peak repetitive reverse voltage             | $V_{RRM}$                         |   | 200         | V     |
| Average rectified forward current           | I <sub>F(AV)</sub>                | T <sub>Sp</sub> = 158 °C                  | 1           | ^     |
| Non-repetitive peak surge current           | I <sub>FSM</sub>                  | T <sub>J</sub> = 25 °C, 6 ms square pulse | 50          | A     |
| Operating junction and storage temperatures | T <sub>J</sub> , T <sub>Stg</sub> |   | -55 to +175 | °C    |

| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                 |   |      |      |      |       |
|--|-----------------|---|------|------|------|-------|
| PARAMETER  | SYMBOL          | TEST CONDITIONS                               | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage  | $V_{BR}, V_{R}$ | I <sub>R</sub> = 100 μA                       | 200  | -    | -    |       |
| Forward voltage per diade  | V               | I <sub>F</sub> = 1 A                          | -    | 0.82 | 0.90 | V     |
| Forward voltage, per diode   | $V_{F}$         | I <sub>F</sub> = 1 A, T <sub>J</sub> = 125 °C | -    | 0.68 | 0.76 |       |
| Reverse leakage current, per diode   |                 | V <sub>R</sub> = V <sub>R</sub> rated         | -    | -    | 2    | μА    |
|  | I <sub>R</sub>  | $T_J = 125$ °C, $V_R = V_R$ rated             | -    | 1    | 8    |       |
| Junction capacitance   | C <sub>T</sub>  | V <sub>R</sub> = 100 V                        | -    | 8    | -    | pF    |



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| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                  |  |   |   |      |      |       |
|---|------------------|--|---|---|------|------|-------|
| PARAMETER   | SYMBOL           | TEST CO  | TEST CONDITIONS   |   | TYP. | MAX. | UNITS |
|   |                  | $I_F = 1.0 \text{ A}, dI_F/dt =$                                       | = 50 A/µs, V <sub>R</sub> = 30 V                                | - | 24   | -    |       |
| Payaraa raaayary tima   | t <sub>rr</sub>  | I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A |   | - | -    | 25   |       |
| Reverse recovery time   |                  | T <sub>J</sub> = 25 °C   |   | - | 15.2 | -    | ns    |
|   |                  | T <sub>J</sub> = 125 °C  |   | - | 21   | -    |       |
| Dealt recovery surrent  |                  | T <sub>J</sub> = 25 °C   | $I_F = 1 A$ ,   | - | 1.38 | -    | ۸     |
| Peak recovery current   | I <sub>RRM</sub> | T <sub>J</sub> = 125 °C  | $dI_F/dt = 200 \text{ A/}\mu\text{s},$<br>$V_R = 200 \text{ V}$ | - | 2    | -    | Α     |
| Reverse recovery charge   | Q <sub>rr</sub>  | T <sub>J</sub> = 25 °C   |   | - | 10.6 | -    | nC    |
|   |                  | T <sub>J</sub> = 125 °C  | ]   | - | 21   | -    | nc    |

| THERMAL - MECHANICAL SPECIFICATIONS            |                                   |   |      |       |      |       |
|--|-----------------------------------|---|------|-------|------|-------|
| PARAMETER                                      | SYMBOL                            | TEST CONDITIONS                                       | MIN. | TYP.  | MAX. | UNITS |
| Maximum junction and storage temperature range | T <sub>J</sub> , T <sub>Stg</sub> |   | -55  | -     | 175  | °C    |
| Thermal resistance, junction to mount          | $R_{thJM}$                        | Device mounted on PCB with 2 x 3.5 mm soldering lands | -    | 11    | 21   | °C/W  |
| Thermal resistance, junction to ambient        | R <sub>thJA</sub>                 | Device mounted on PCB with recommended pad size       | -    | -     | 125  | °C/W  |
| Approximate weight                             |                                   |   |      | 0.07  |      | g     |
| Approximate weight                             |                                   |   |      | 0.002 |      | oz.   |
| Marking device                                 |                                   | Case style SMA (DO-214AC)                             |      | 1     | H2   |       |

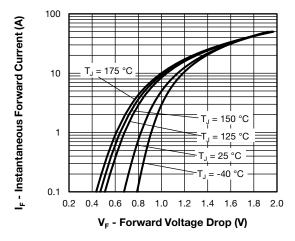


Fig. 1 - Typical Forward Voltage Drop Characteristics

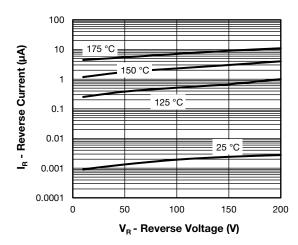


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



180

175

170

165

160

155

150 0

Allowable Case Temperature (°C)

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D = 0.02D = 0.05D = 0.1D = 0.2D = 0.5DC

2

2.5

3

3.5

1.5

 $I_{\text{F(AV)}}$  - Average Forward Current (A)

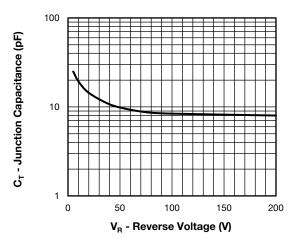
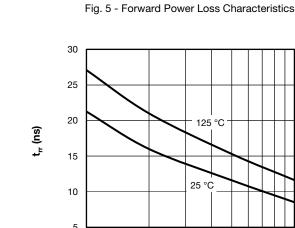


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

DC

0.8

1.2



3

2.5

2

1.5

0.5

0

0

0.5

Average Power Loss (W)

**RMS** limit

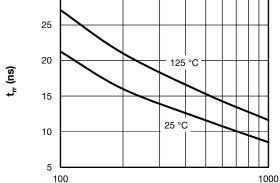


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

0.6

I<sub>F(AV)</sub> - Average Forward Current (A)

Square wave (D = 0.50)Rated V<sub>R</sub> applied

0.4

See note (1)

0.2

Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

dl<sub>F</sub>/dt (A/µs)

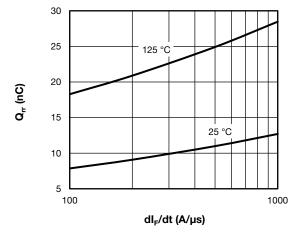
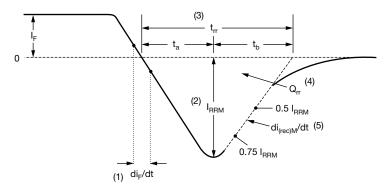


Fig. 7 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $^{(1)}$  Formula used:  $T_{C} = T_{J}$  - (Pd + Pd\_{REV}) x  $R_{thJC};$ Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV}$  = inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

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- di<sub>F</sub>/dt rate of change of current through zero crossing
- (2) I<sub>RRM</sub> peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $\mathbf{Q}_{\rm rr}$  area under curve defined by  $\mathbf{t}_{\rm rr}$  and  $\mathbf{I}_{\rm RRM}$

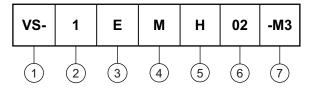
$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5)  $di_{(rec)M}/dt$  - peak rate of change of current during  $t_b$  portion of  $t_{rr}$ 

Fig. 8 - Reverse Recovery Waveform and Definitions

#### ORDERING INFORMATION TABLE

**Device code** 



- Vishay Semiconductors product
- 2 Current rating (1 = 1 A)
- Circuit configuration:

E = single diode

4 - M = SMA package

5 - Process type,

H = hyperfast recovery

6 - Voltage code (02 = 200 V)

7 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example)   |      |      |                                   |  |  |
|--|------|------|-----------------------------------|--|--|
| PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION |      |      |                                   |  |  |
| VS-1EMH02-M3/5AT   | 7500 | 7500 | 13"diameter plastic tape and reel |  |  |

| LINKS TO RELATED DOCUMENTS                 |                          |  |  |  |
|--|--------------------------|--|--|--|
| Dimensions <u>www.vishay.com/doc?95400</u> |                          |  |  |  |
| Part marking information                   | www.vishay.com/doc?95472 |  |  |  |
| Packaging information                      | www.vishay.com/doc?95404 |  |  |  |
| SPICE model                                | www.vishay.com/doc?96376 |  |  |  |

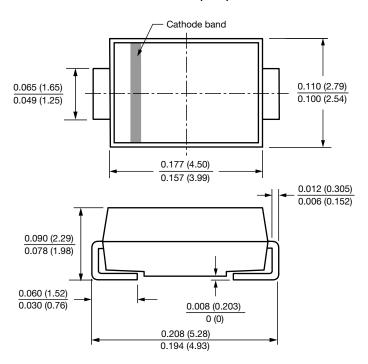


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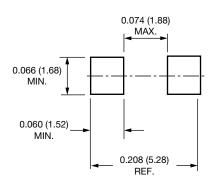
### **SMA**

### **DIMENSIONS** in inches (millimeters)

### DO-214AC (SMA)



### **Mounting Pad Layout**







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